TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM3GZ47, **SM3JZ47**

AC POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage: VDRM = 400V, 600V
- R.M.S On-State Current: I_T (RMS) = 3A
- High Commutating (dv / dt)
- Isolation Voltage: VISOL = 1500V AC

ABSOLUTE MAXIMUM RATINGS

CHARACTERIS	SYMBOL	RATING	THAU		
Repetitive Peak Off-State Voltage	SM3GZ47	V2211	400		
	SM3JZ47	V_{DRM}	600		
R.M.S On-State Current (Full Sine Waveform Tc =	I _{T (RMS)}	3	A		
Peak One Cycle Surge C Current (Non-Repetitive)	I _{TSM}	30 (50Hz)	A		
, , ,	ı ² t	33 (60Hz)	A ² s		
I [∠] t Limit Value (t = 1~10n	ns)	1 t	4.5	AS	
Critical Rate of Rise of O Current	di / dt	50	A / µs		
Peak Gate Power Dissipa	P _{GM}	5	w/		
Average Gate Power Dis	Pg (AV)	0.5	w		
Peak Gate Voltage	(V _{GM}) 10		// v		
Peak Gate Current	IGM	2	A		
Junction Temperature	//)Tj	-40~125	°C		
Storage Temperature Ra	T _{stg}	-40~125	°C		
Isolation Voltage (AC, t	⊃ V _{ISOL}	1500	V		

Weight: 1.7 g (typ.)

Note 1: di / dt test condition VDRM = 0,5×Rated

I_{TM} ≤ 4.5Å

t_{qw} ≥ 10µs

t_{gr} ≤ 250ns

 $\log_p = \log_T \times 20$

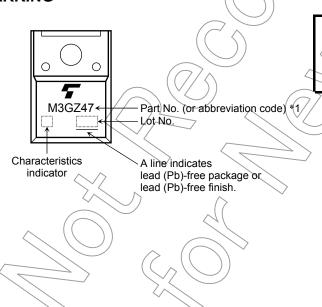
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST (CONDITION	MIN	TYP.	MAX	UNIT
Repetitive Peak Off-State Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μΑ
Gate Trigger Voltage	I	V _{GT}	V _D = 12V R _L = 20Ω	T2 (+), Gate (+)	_	_	1.5	V
	II			T2 (+), Gate (-)	\nearrow	_	1.5	
	III			T2 (-), Gate (-)	(-)	7	1.5	
	IV			T2 (-), Gate (+)) —	-	
Gate Trigger Current	I	lgт	V _D = 12V R _L = 20Ω	T2 (+), Gate (+)		_	20	- mA
	II			T2 (+), Gate (-)	<u> </u>	_	20	
	III			T2 (-), Gate (-)	· –	_	20	
	IV			T2 (~), Gate (+)	_			
Peak On-State Voltage		V _{TM}	I _{TM} = 4.5A	4()	_	4	1,5	V
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	7	,	V
Holding Current		lΗ	V _D = 12V, I _{TM} = 1A		-((30	mA
Thermal Resistance Rth (j-		R _{th (j-c)}	Junction to Case, AC		(-	(4)	4.2	°C / W
Critical Rate of Rise of Off–State Voltage dv / dt VDRM = Rated, Ty = 125°C Exponential Rise				300	_	V / µs		
Critical Rate of Rise of Off-State Voltage at Commutation		(dv / dt) c	VDRM = 400V, T _j = 125°C (di /dt) c = -2.0A / ms		10	_	_	V / µs

MARKING



Part No.

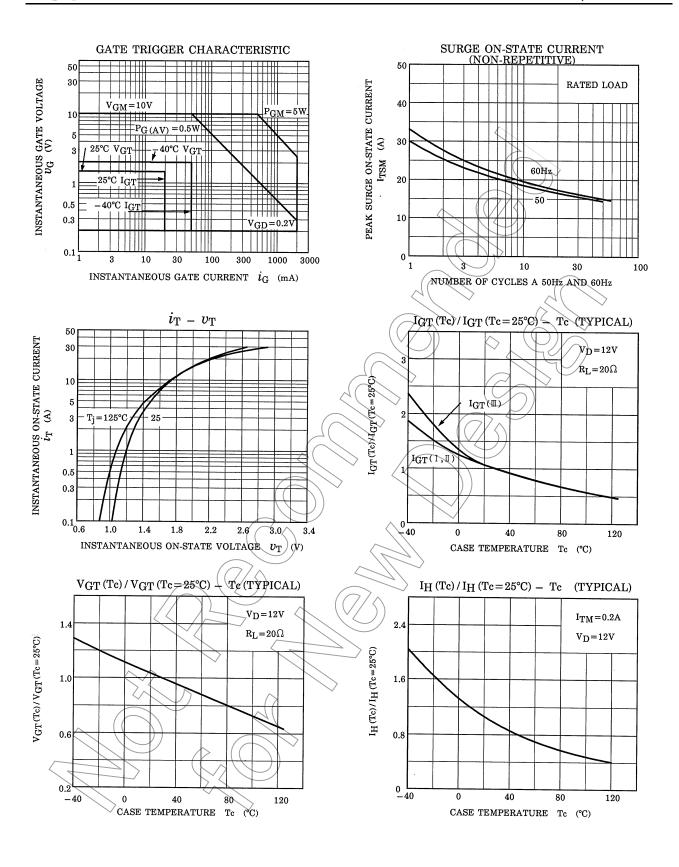
(or abbreviation code) M3GZ47

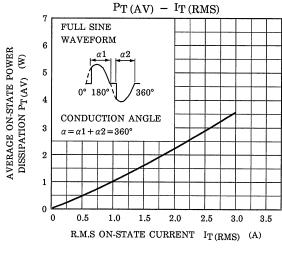
M3JZ47

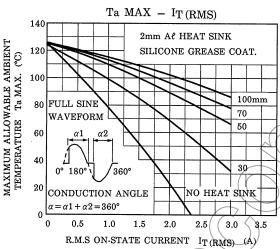
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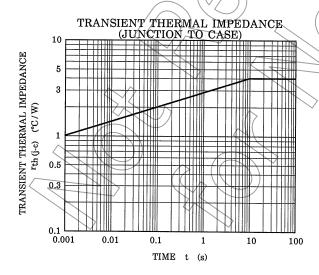
SM3GZ47

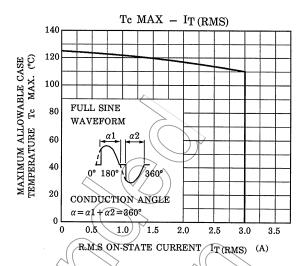
SM3JZ47

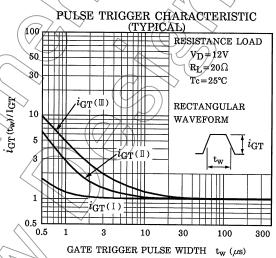












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